

# ACTS573MS

# Radiation Hardened Octal Three-State Transparent Latch

#### January 1996

## Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96725 and Intersil's QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Single Event Upset (SEU) Immunity: <1 x 10<sup>-10</sup> Errors/Bit/Day (Typ)

- Latch-Up Free Under Any Conditions
- Military Temperature Range ......-55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range ..... 4.5V to 5.5V
- Input Logic Levels
  - VIL = 0.8V Max
  - VIH = VCC/2 Min
- Input Current  $\leq$  1µA at VOL, VOH

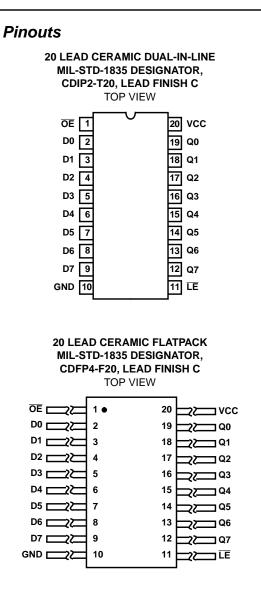
• Fast Propagation Delay ..... 18ns (Max), 12ns (Typ)

## Description

The Intersil ACTS573MS is a Radiation Hardened Octal Transparent Latch with an active low output enable. The outputs are transparent to the inputs when the latch enable ( $\overline{\text{LE}}$ ) is High. When the latch goes low the data is latched. The output enable controls the three-state outputs. When the output enable pins ( $\overline{\text{OE}}$ ) are high the output is in a high impedance state. The latch operation is independent of the state of output enable.

The ACTS573MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of a radiation hardened, high-speed, CMOS/SOS Logic family.

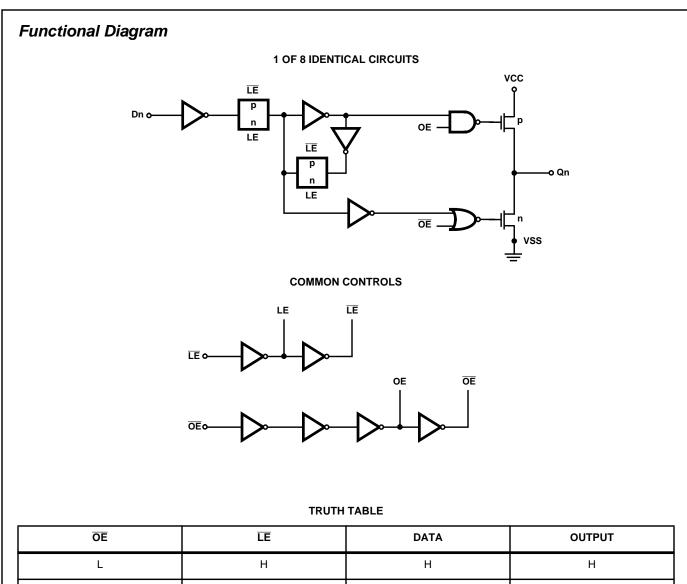
The ACTS573MS is supplied in a 20 lead Ceramic Flatpack (K suffix) or a Ceramic Dual-In-Line package (D suffix).



## **Ordering Information**

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9672501VRC	-55°C to +125°C	MIL-PRF-38535 Class V	20 Lead SBDIP
5962F9672501VXC	-55°C to +125°C	MIL-PRF-38535 Class V	20 Lead Ceramic Flatpack
ACTS573D/Sample	25°C	Sample	20 Lead SBDIP
ACTS573K/Sample	25°C	Sample	20 Lead Ceramic Flatpack
ACTS573HMSR	25°C	Die	Die

CAUTION: These devices are sensitive to electrostatic discharge; follow proper IC Handling Procedures. 1-888-INTERSIL or 321-724-7143 | Copyright © Intersil Corporation 1999



ŌE	LE	DATA	OUTPUT
L	Н	Н	н
L	Н	L	L
L	L	I	L
L	L	h	н
Н	Х	Х	Z

NOTE: L = Low Logic Level, H = High Logic Level, X = Don't Care, Z = High Impedance, I = Low Voltage Level Prior to High-to-Low Latch Enable Transition, h = High Voltage Level Prior to High-to-Low Latch Enable Transition.

All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site http://www.intersil.com

## **Die Characteristics**

#### DIE DIMENSIONS:

102 mils x 102 mils 2,600mm x 2,600mm

#### **METALLIZATION:**

Type: AlSi Metal 1 Thickness: 7.125kÅ ±1.125kÅ Metal 2 Thickness: 9kÅ ±1kÅ

#### **GLASSIVATION:**

Type: SiO<sub>2</sub> Thickness: 8kÅ ±1kÅ

# WORST CASE CURRENT DENSITY:

 $<2.0 \text{ x} 10^5 \text{ A/cm}^2$ 

#### BOND PAD SIZE:

> 4.3 mils x 4.3 mils

> 110µm x 110µm

## Metallization Mask Layout



